

**GUJARAT TECHNOLOGICAL UNIVERSITY****BE - SEMESTER-VI (NEW) EXAMINATION – WINTER 2018****Subject Code:2161101****Date:30/11/2018****Subject Name:VLSI Technology & Design****Time: 02:30 PM TO 05:00 PM****Total Marks: 70****Instructions:**

1. Attempt all questions.
2. Make suitable assumptions wherever necessary.
3. Figures to the right indicate full marks.

- Q.1** (a) Explain VLSI Design flow using Y-chart. **03**  
(b) Discuss physical parameters affecting the threshold voltage of MOS structure. **04**  
(c) Derive the MOSFET drain current equation while MOSFET is operating in linear region using GCA. **07**
- Q.2** (a) Draw mask layout of the CMOS Inverter and indicate various terms. **03**  
(b) In CMOS inverter circuit, enhancement type MOSFET devices are used and if  $V_{DD}$  is reduced below  $V_{T0,n} + |V_{T0,p}|$ , explain how the output voltage will follow the change in input voltage. Draw VTC and explain its behavior. **04**  
(c) Discuss fabrication process of n-channel MOSFET in detail. **07**
- OR**
- (c) Draw Resistive-load inverter using n-channel MOSFET. Derive expressions of critical voltages  $V_{OL}$ ,  $V_{OH}$ ,  $V_{IL}$ , and  $V_{IH}$  of Resistive-load inverter. **07**
- Q.3** (a) Compare Semi-custom and Full custom VLSI design style. **03**  
(b) What do you mean by MOSFET Scaling? Explain Constant-field Scaling. **04**  
(c) "The average power dissipation of the CMOS Inverter is proportional to switching frequency." Explain it with necessary mathematical analysis. **07**
- OR**
- Q.3** (a) Give comparison between FPGA and CPLD. **03**  
(b) Describe Accumulation and Inversion process for the MOS system under external bias. **04**  
(c) Derive expression of  $\tau_{PHL}$  for CMOS Inverter where input is ideal step input. **07**
- Q.4** (a) Explain CMOS Ring Oscillator circuit in brief. **03**  
(b) Draw different representations of the CMOS Transmission Gate. Implement  $2 \times 1$  Multiplexer circuit using two CMOS TGs and one inverter. **04**  
(c) Explain cascading problem observed in dynamic CMOS logic. What are the different approaches to solve this problem? **07**
- OR**
- Q.4** (a) Discuss VTC of CMOS Inverter with operating region. **03**  
(b) Implement Boolean function  $Z = AB + C(D + E)$  using CMOS logic circuit **04**  
(c) Discuss need of Voltage Bootstrapping and explain dynamic Voltage Bootstrapping with necessary mathematical analysis. **07**
- Q.5** (a) List out possible physical, electrical and logical faults observed at Chip Testing. **03**  
(b) Define *Latch-up*. Enlist guidelines for avoiding Latch-up. **04**  
(c) Explain D latch with CMOS implementation. **07**
- OR**
- Q.5** (a) Draw NAND gate based CMOS SR latch circuit. **03**  
(b) Explain various Clock Distribution Networks. **04**  
(c) Explain Ad Hoc Testable Design Techniques. **07**

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